

## Accepted Manuscript

Title: Aspect Ratio Dependent Cold Cathode Emission from Vertically Aligned Hydrophobic Silicon Nanowires

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PII: S0025-5408(17)32523-0  
DOI: <http://dx.doi.org/10.1016/j.materresbull.2017.08.051>  
Reference: MRB 9530

To appear in: *MRB*

Received date: 29-6-2017  
Revised date: 23-8-2017  
Accepted date: 26-8-2017

Please cite this article as: U.Ray, D.Banerjee, B.Das, N.S.Das, S.K.Sinha, K.K.Chattopadhyay, Aspect Ratio Dependent Cold Cathode Emission from Vertically Aligned Hydrophobic Silicon Nanowires, Materials Research Bulletin <http://dx.doi.org/10.1016/j.materresbull.2017.08.051>

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## Aspect Ratio Dependent Cold Cathode Emission from Vertically Aligned Hydrophobic Silicon Nanowires

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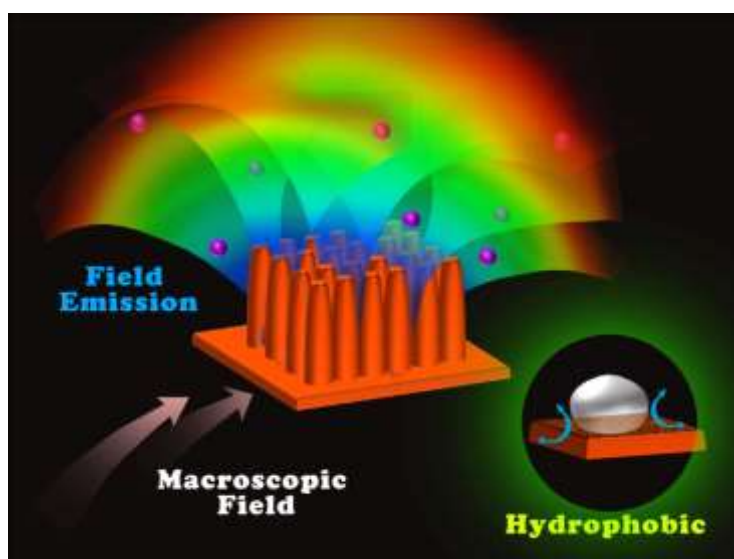
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### Graphical abstract



### Highlights

- Vertically aligned silicon nanowires (SiNWs) were grown on silicon substrate.
- The aspect ratio was tailored by varying etching time.
- The as prepared sample was made superhydrophobic by simple chemical treatment.
- As prepared samples show good cold emission property.

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